

Remarks:

Applicants respectfully request that this amendment be entered, and that their subject U.S. Patent Application be passed to issuance in view thereof.

In the Office Action, claim 45 has been amended to adopt the Examiner's suggestion, and claims 20 and 46 have been amended to address the 112 rejections of record. Accordingly, Applicants respectfully submit that the objections and rejections appearing on the second page of the Office Action have been traversed.

In the Office Action, the pending claims stand rejected on 102 and 103 grounds, based on the Long et al. patent (U.S. Patent No. 6,306,710 hereinafter referred to as "Long"). In response, Applicants respectfully submit that the Long patent neither teaches nor suggests the invention as recited in the claims as presented herein. As Long shows in FIGS. 14 and 15, second conductive material 286 has a thickness less than the first conductive material. Referring to FIGS. 14 and 15 of Long, what Examiner refers to as a second conductive material (gate silicide) 286 is formed on first conductive material 230. Long forms silicide layers 282, 284 and 286 according to processes known to one of ordinary skill in the art (column 9, lines 9-13). It is well known in the art to form a metal layer and anneal to form a metal silicide simultaneously over source 272, drain 274 and gate 230 regions. Thus, the thickness of second conductive material 286 is determined by the thickness of silicide layers 282, 284 since the thickness of silicide layers 282, 284 is limited by the depth of drain and source contact junctions 272, 274. For a given depth of the drain and source contact junctions 272, 274, silicide layers 282, 284 must be less than the depth of the junctions 272, 274. As the trend in semiconductor devices is to increase speed by reducing device size, the depth of source/drain junctions is decreasing and since second conductive material 286 is formed simultaneously with silicide layers 282, 284, Long does not independently control the thickness of second conductive material 286. Thus, Long provides no teaching or suggestion for the second conductive material having a thickness greater than a

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thickness of the first conductive material.

Claims 20 and 46 have been amended to more clearly recite the correlation in the invention between the height (i.e. sidewall length) differences between the upper and lower portions of the T gate. This aspect of the invention is discussed at, for example, page 9, lines 21-23 and FIGS. 3a, 4, 5 of the subject specification. Applicants invention provides for a T-shaped gate having a large area upper portion that avoids increasing gate resistance when the lower portion is reduced. Since this feature of the invention is neither taught nor suggested by Long, alone or in combination with the other references of record, Applicants respectfully submit that the prior art rejections of record to claims 20 and 46 (as well as the other pending claims depending thereon) have been traversed.

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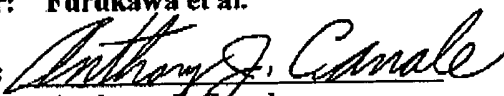
Conclusion:

Accordingly, Applicants respectfully request entry of the present Amendment and passage of their subject application to issuance in view thereof. Should the Examiner have any comments, questions, or suggestions, please do not hesitate to contact the undersigned agent at the telephone number and/or email address set forth below.

Respectfully submitted,

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